



Preliminary

TSM4392

30V N-Channel MOSFET



- Pin Definition:**
1. Source
 2. Source
 3. Source
 4. Gate
 - 5, 6, 7, 8. Drain

PRODUCT SUMMARY

| V_{DS} (V) | $R_{DS(on)}$ (m Ω) | I_D (A) |
|--------------|----------------------------|-----------|
| 30 | 11.5 @ $V_{GS} = 10V$ | 12.5 |
| | 16.5 @ $V_{GS} = 4.5V$ | 10 |

Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

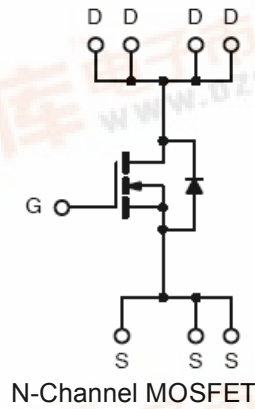
Application

- High-Side DC/DC Conversion
- Notebook
- Sever

Ordering Information

| Part No. | Package | Packing |
|--------------|---------|--------------------|
| TSM4392CS RL | SOP-8 | 2.5Kpcs / 13" Reel |

Block Diagram



Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|---|----------------|--------------|------|
| Drain-Source Voltage | V_{DS} | 30 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | V |
| Continuous Drain Current | I_D | 12.5 | A |
| Pulsed Drain Current | I_{DM} | 50 | A |
| Continuous Source Current (Diode Conduction) ^{a,b} | I_S | 2.7 | A |
| Maximum Power Dissipation | P_D | Ta = 25°C | 3.0 |
| | | Ta = 75°C | 1.9 |
| Operating Junction Temperature | T_J | +150 | °C |
| Operating Junction and Storage Temperature Range | T_J, T_{STG} | - 55 to +150 | °C |

Thermal Performance

| Parameter | Symbol | Limit | Unit |
|--|-----------------|-------|------|
| Junction to Case Thermal Resistance | $R_{\theta JF}$ | 25 | °C/W |
| Junction to Ambient Thermal Resistance (PCB mounted) | $R_{\theta JA}$ | 50 | °C/W |

Notes:

a. Pulse width limited by the Maximum junction temperature

b. Surface Mounted on FR4 Board, t ≤ 10 sec.

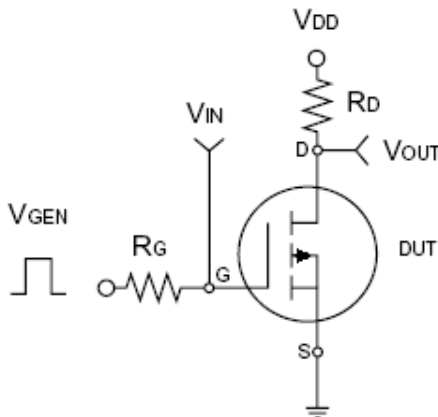


Electrical Specifications (Ta = 25°C unless otherwise noted)

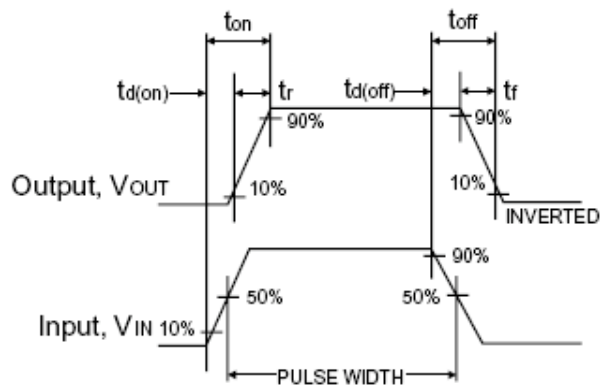
| Parameter | Conditions | Symbol | Min | Typ | Max | Unit |
|---|--|--------------|-----|------|-----------|------------|
| Static | | | | | | |
| Drain-Source Breakdown Voltage | $V_{GS} = 0V, I_D = 250\mu A$ | BV_{DSS} | 30 | -- | -- | V |
| Gate Threshold Voltage | $V_{DS} = V_{GS}, I_D = 250\mu A$ | $V_{GS(TH)}$ | 1 | 1.8 | 3 | V |
| Gate Body Leakage | $V_{GS} = \pm 20V, V_{DS} = 0V$ | I_{GSS} | -- | -- | ± 100 | nA |
| Zero Gate Voltage Drain Current | $V_{DS} = 24V, V_{GS} = 0V$ | I_{DSS} | -- | -- | 1.0 | μA |
| On-State Drain Current ^a | $V_{DS} \geq 5V, V_{GS} = 10V$ | $I_{D(ON)}$ | 30 | -- | -- | A |
| Drain-Source On-State Resistance ^a | $V_{GS} = 10V, I_D = 12.5A$ | $R_{DS(ON)}$ | -- | 9 | 11.5 | m Ω |
| | $V_{GS} = 4.5V, I_D = 10A$ | | -- | 13 | 16.5 | |
| Forward Transconductance ^a | $V_{DS} = 15V, I_D = 12.5A$ | g_{fs} | -- | 40 | -- | S |
| Diode Forward Voltage | $I_S = 2.7A, V_{GS} = 0V$ | V_{SD} | -- | 0.85 | 1.3 | V |
| Dynamic^b | | | | | | |
| Total Gate Charge | $V_{DS} = 15V, I_D = 12.5A, V_{GS} = 10V$ | Q_g | -- | 26 | -- | nC |
| Gate-Source Charge | | Q_{gs} | -- | 6 | -- | |
| Gate-Drain Charge | | Q_{gd} | -- | 5 | -- | |
| Input Capacitance | $V_{DS} = 15V, V_{GS} = 0V, f = 1.0MHz$ | C_{iss} | -- | 2134 | -- | pF |
| Output Capacitance | | C_{oss} | -- | 343 | -- | |
| Reverse Transfer Capacitance | | C_{rss} | -- | 134 | -- | |
| Switching^c | | | | | | |
| Turn-On Delay Time | $V_{DD} = 15V, R_L = 15\Omega, I_D = 1A, V_{GEN} = 10V, R_G = 6\Omega$ | $t_{d(on)}$ | -- | 17 | -- | nS |
| Turn-On Rise Time | | t_r | -- | 3.5 | -- | |
| Turn-Off Delay Time | | $t_{d(off)}$ | -- | 40 | -- | |
| Turn-Off Fall Time | | t_f | -- | 6 | -- | |

Notes:

- a. pulse test: PW $\leq 300\mu S$, duty cycle $\leq 2\%$
- b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.

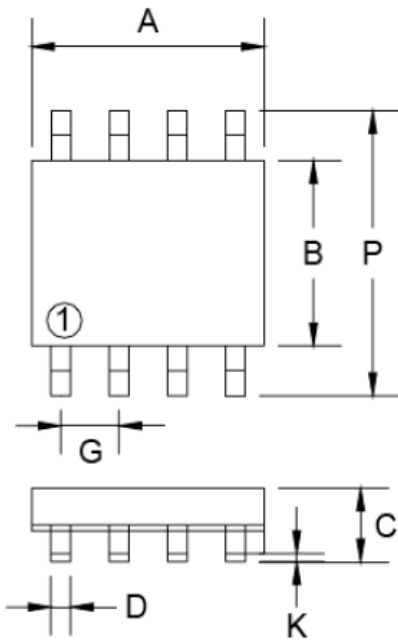


Switching Test Circuit



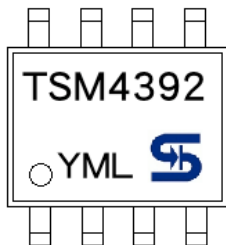
Switchin Waveforms

SOP-8 Mechanical Drawing



| SOP-8 DIMENSION | | | | |
|-----------------|-------------|------|---------|-------|
| DIM | MILLIMETERS | | INCHES | |
| | MIN | MAX | MIN | MAX. |
| A | 4.80 | 5.00 | 0.189 | 0.196 |
| B | 3.80 | 4.00 | 0.150 | 0.157 |
| C | 1.35 | 1.75 | 0.054 | 0.068 |
| D | 0.35 | 0.49 | 0.014 | 0.019 |
| F | 0.40 | 1.25 | 0.016 | 0.049 |
| G | 1.27BSC | | 0.05BSC | |
| K | 0.10 | 0.25 | 0.004 | 0.009 |
| M | 0° | 7° | 0° | 7° |
| P | 5.80 | 6.20 | 0.229 | 0.244 |
| R | 0.25 | 0.50 | 0.010 | 0.019 |

Marking Diagram



- Y = Year Code
- M = Month Code
(A=Jan, B=Feb, C=Mar, D=Apr, E=May, F=Jun, G=Jul, H=Aug, I=Sep, J=Oct, K=Nov, L=Dec)
- L = Lot Code



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